N-Ch and P-Ch Fast Switching MOSFETs

★ 100% EAS Guaranteed
★ Green Device Available
★ Super Low Gate Charge
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

Product Summary

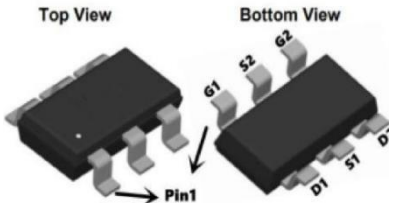
Green

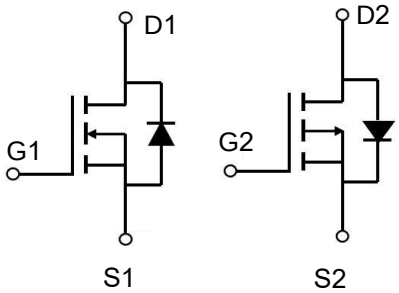
BVDSS	RDSON	ID
40V	26mΩ	5A
-40V	60mΩ	-5.5A

Description

The **XR6G04L** is the high performance complementary N-ch and P-ch MOSFETs with high cell density, whichprovide excellent RDSON and gate charge for most of the synchronous buck converter applications .
The X**R6G04L** meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

SOT 23-6L Pin Configurations





Applications

- Power management in half bridge and inverters
- DC-DC Converter
- Load Switch

Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage	40	-40	V
V_{GS}	Gate-Source Voltage	±20	±20	V
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ 10V[1]	5	-4	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ 10V[1]	3.6	-3.2	A
I_{DM}	Pulsed Drain Current[2]	14.5	-15	A
EAS	Single Pulse Avalanche Energy[3]	28	26	mJ
I_{AS}	Avalanche Current	10.8	- 7.2	A
P_D@T_C=25°C	Total Power Dissipation[4]	2.5	2.1	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	°C

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} =40V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0	1.5	2.2	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}=10V, I_D=4A	-	26	40	mΩ
		V_{GS}=4.5V, I_D=3A	-	35	60	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=20V, V_{GS}=0V, f=1.0MHz	-	435	-	pF
C_{oss}	Output Capacitance		-	58	-	pF
C_{rss}	Reverse Transfer Capacitance		-	35	-	pF
Q_g	Total Gate Charge	V_{DS}=20V, I_D=3A, V_{GS}=10V	-	11	-	nC
Q_{gs}	Gate-Source Charge		-	2	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	2.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=20V, I_D=4A, R_L=1Ω, R_{GEN}=3Ω, V_{GS}=10V	-	10	-	ns
t_r	Turn-on Rise Time		-	8	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	29	-	ns
t_f	Turn-off Fall Time		-	12	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=5A	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	T_J=25℃, I_F=5A,dI/dt=100A/μs	-	20	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	11	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}= 0V, I_D= -250μA	-40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}= -40V, V_{GS}= 0V	-	-	-1	μA
Gate-Body Leakage	I_{GSS}	V_{DS}= 0V, V_{GS}= ±20V	-	-	±100	nA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D= -250μA	-1.2	-1.5	-2.5	V
Drain-Source on-Resistance[3]	$R_{DS(on)}$	V_{GS}= -10V,I_D= -5A	-	60	80	mΩ
		V_{GS}= -4.5V,I_D= -4A	-	71	92	
Dynamic Characteristics[4]						
Input Capacitance	C_{iss}	V_{GS} = 0V ,V_{DS} = -20V, f=1.0MHz	-	553	-	pF
Output Capacitance	C_{oss}		-	50	-	
Reverse Transfer Capacitance	C_{rss}		-	42	-	
Switching Characteristics[4]						
Total Gate Charge	Q_g	V_{GS}= -10V ,V_{DS}= -20V, I_D= -5A	-	11.8	-	nC
Gate-Source Charge	Q_{gs}		-	2.2	-	
Gate-Drain Charge	Q_{gd}		-	3	-	
Turn-on Delay Time	$t_{d(on)}$	V_{DS}= -20V, V_{GS}= -10V R_L= 2.5Ω, R_G= 3Ω	-	7	-	ns
Rise Time	t_r		-	6.5	-	
Turn-off Delay Time	$t_{d(off)}$		-	24	-	
Fall Time	t_f		-	7.8	-	
Drain-Source Body Diode Characteristics						
Body Diode voltage[3]	V_{DS}	I_S= -5A,V_{GS}=0V	-	-	-1.2	V
Continuous Source Current	I_S		-	-	-5.5	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Performance Characteristics-N

Figure1: Output Characteristics

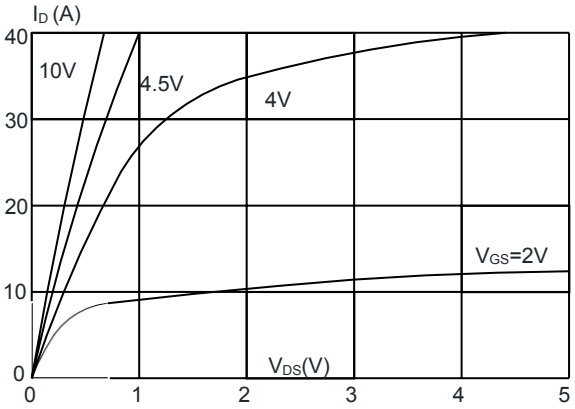


Figure 2: Typical Transfer Characteristics

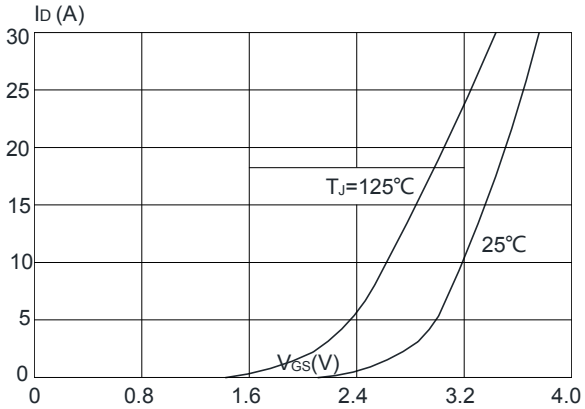


Figure 3: On-resistance vs. Drain Current

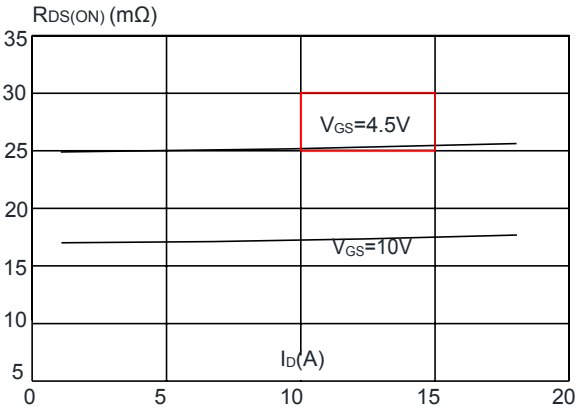


Figure 4: Body Diode Characteristics

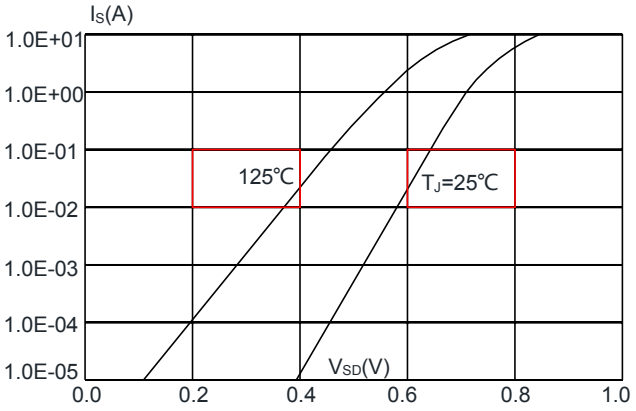


Figure 5: Gate Charge Characteristics

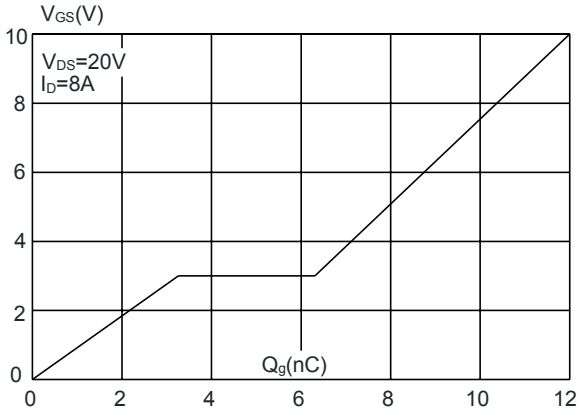


Figure 6: Capacitance Characteristics

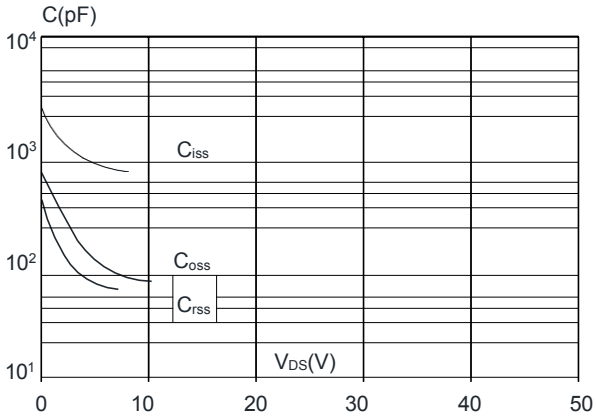


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

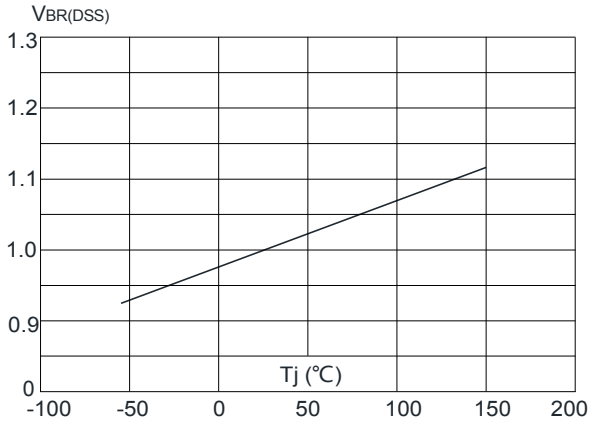


Figure 8: Normalized on Resistance vs. Junction Temperature

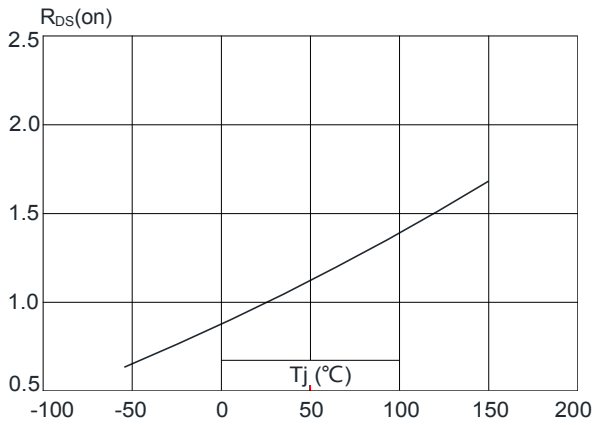


Figure 9: Maximum Safe Operating Area

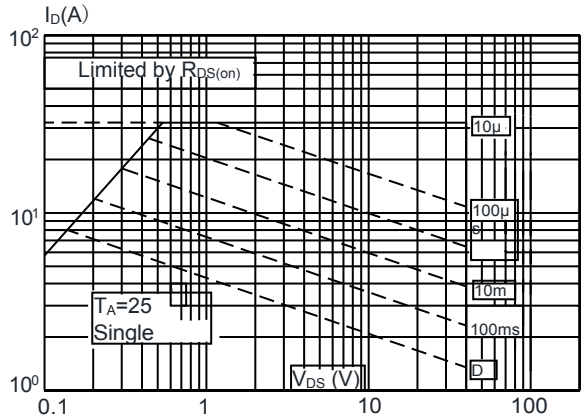


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

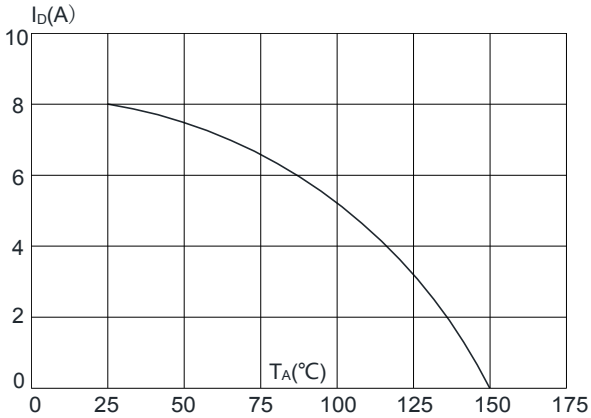
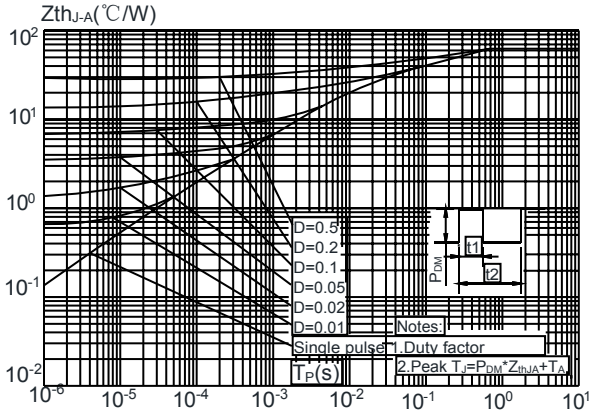


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Typical Performance Characteristics-P

Figure1: Output Characteristics

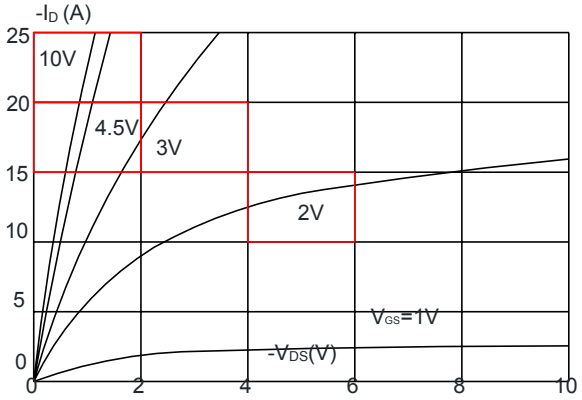
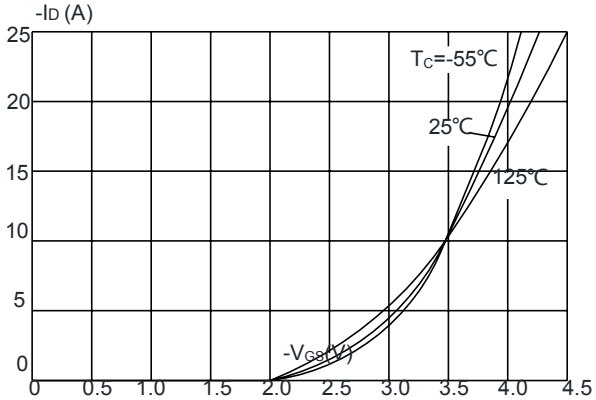


Figure 2: Typical Transfer Characteristics



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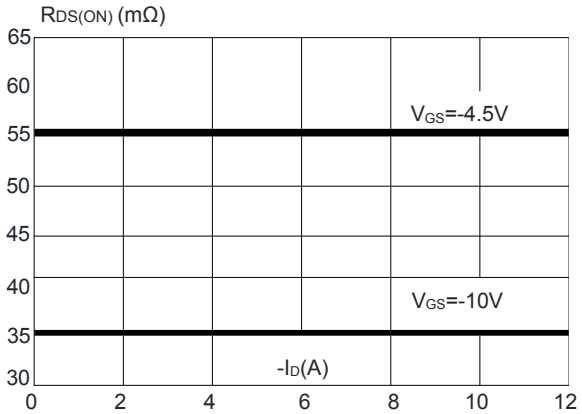


Figure 4: Body Diode Characteristics

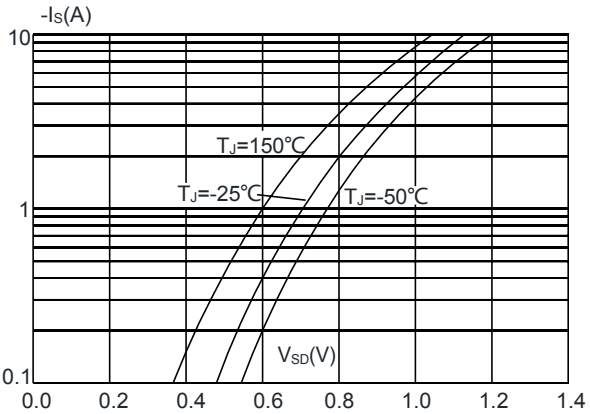


Figure 5: Gate Charge Characteristics

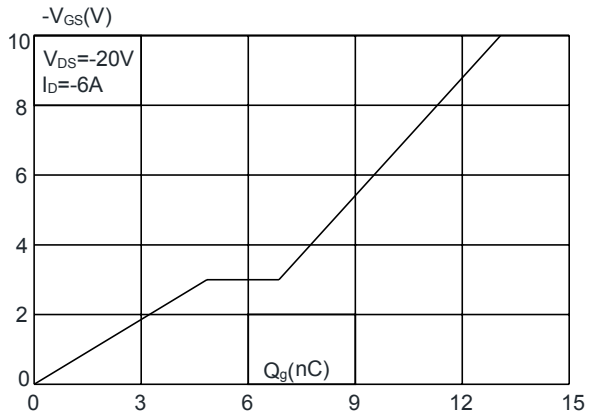
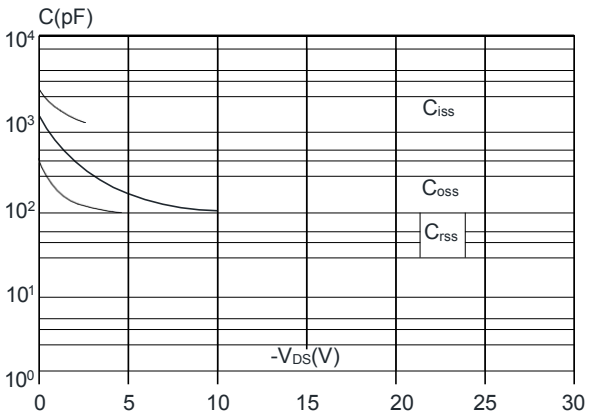


Figure 6: Capacitance Characteristics



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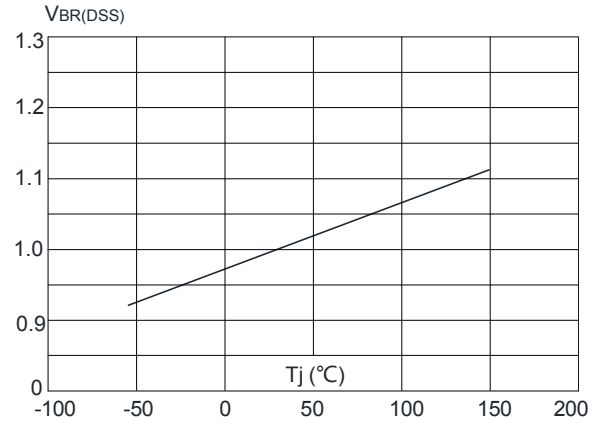
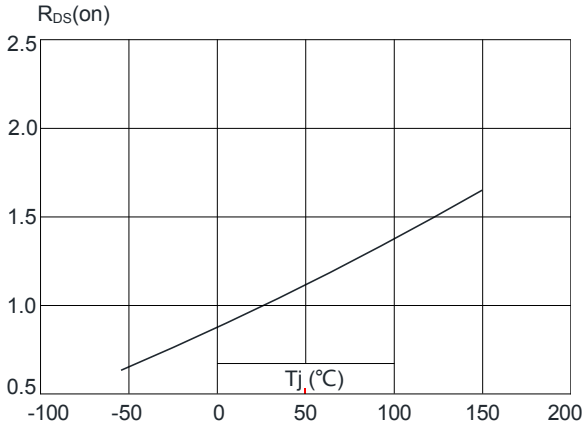


Figure 8: Normalized on Resistance vs. Junction Temperature



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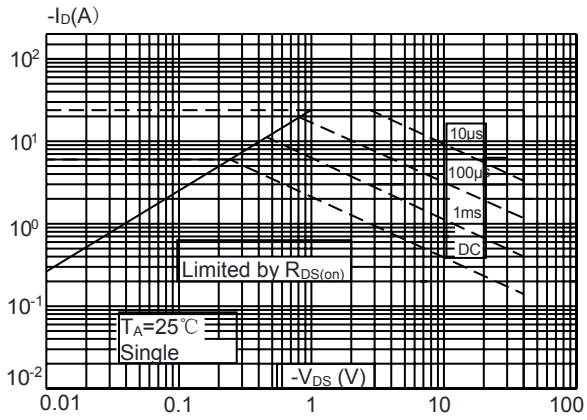


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

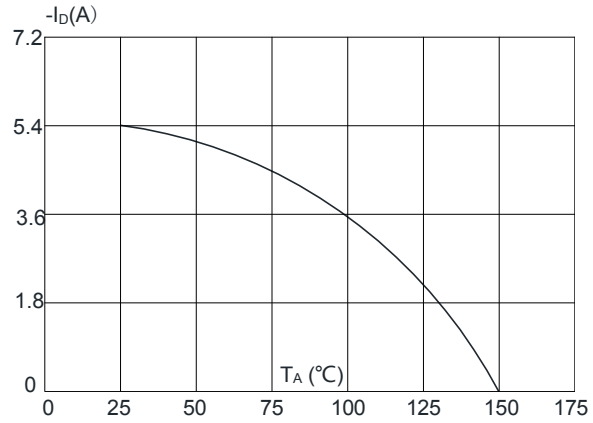
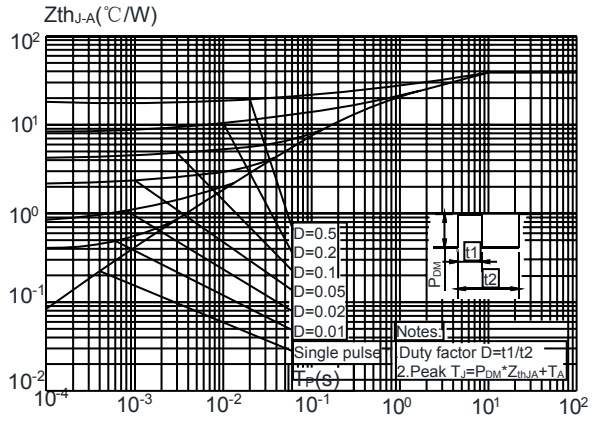
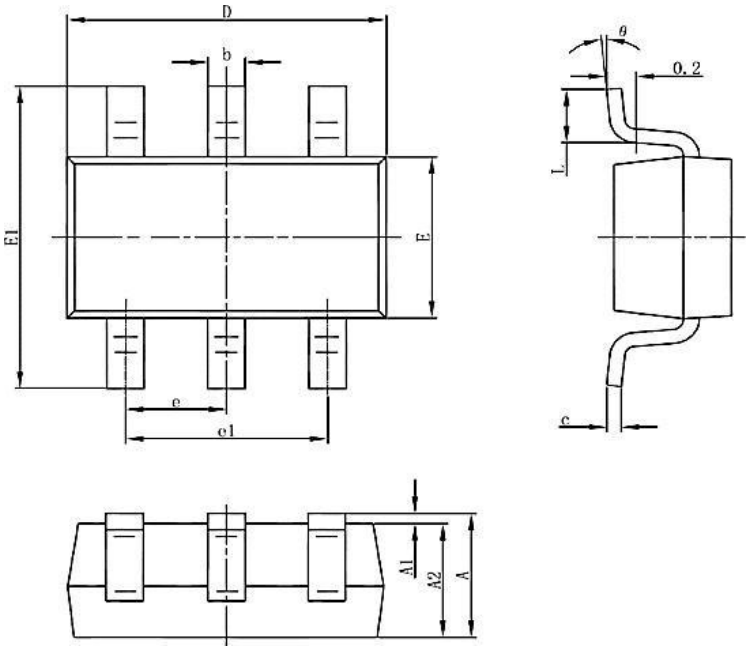


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Package Mechanical Data-SOT23-6L-Double



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
C	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950（BSC）		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0	8	0	8